

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims**

1. (Currently amended) A plasma processing reactor comprising:
  - a chamber having a removable substrate support asymmetric about a vertical axis of said chamber;
  - a RF power supply coupled to said chamber, said RF power supply adapted to supply RF power to said chamber to generate a plasma therein; and
  - a coating of an electrically resistive material selectively disposed on at least one of the substrate support ~~or~~ and a surface of said chamber, the electrically resistive material having an RF impedance different from an RF impedance of an underlying base material of said chamber.
2. (Previously Presented) The plasma processing reactor of claim 1, wherein said material includes varying composition to vary the RF impedance azimuthally.
3. (Previously Presented) The plasma processing reactor of claim 1, wherein said material has a selectively varying thickness to vary the RF impedance azimuthally.
4. (Previously Presented) The plasma processing reactor of claim 1, wherein said material is disposed in various shapes to vary the RF impedance azimuthally.
5. (Previously Presented) The plasma processing reactor of claim 1, wherein said material further comprises a plurality of film strips each having a variable thickness dimension.

6. (Previously Presented) The plasma processing reactor of claim 1, wherein said material further includes a plurality of film strips azimuthally positioned.

7. (Previously Presented) The plasma processing reactor of claim 1, wherein said material is selectively applied prior to processing a portion of a surface of said removable substrate support within said chamber.

8. (Previously Presented) The plasma processing reactor of claim 1, wherein said electrically resistive material includes Nickel.

9. (Previously Presented) The plasma processing reactor of claim 1, wherein said electrically resistive material includes Copper.

10. (Previously Presented) The plasma processing reactor of claim 1 wherein said material is plated to at least one of the substrate support or a surface of said chamber.

11-30. (Cancelled)

31. (New) The plasma processing reactor of claim 1 wherein said at least one of said substrate support and said surface of said chamber represents said substrate support.

32. (New) The plasma processing reactor of claim 1 wherein said at least one of said substrate support and said surface of said chamber represents said substrate support and said surface of said chamber.

33. (New) The plasma processing reactor of claim 1 wherein said electrical resistive material is a continuous film coated on said substrate support and said surface of said chamber.

34. (New) The plasma processing reactor of claim 1 wherein said at least one of said substrate support and said surface of said chamber represents a portion of inner walls of said chamber.

35. (New) The plasma processing reactor of claim 1 wherein said RF impedance of said electrically resistive material is higher than said RF impedance of said underlying base material of said chamber.

36. (New) A plasma processing reactor comprising:

a chamber;

a substrate support coupled with said chamber; and

a coating of an electrically resistive material selectively disposed on at least one of said substrate support and a surface of said chamber, an RF impedance of said coating being higher than an RF impedance of an underlying base material of said chamber.

37. (New) The plasma processing reactor of claim 36 wherein said coating is a film coated on said substrate support.

38. (New) The plasma processing reactor of claim 36 wherein said coating is a continuous film coated on said substrate support and said surface of said chamber.

39. (New) The plasma processing reactor of claim 36 wherein said coating is a continuous film coated on a portion of inner walls of said chamber.

40. (New) The plasma processing reactor of claim 36 wherein said coating is a filmstrip having a rectangular shape with a larger side perpendicular to a plane of said substrate support.